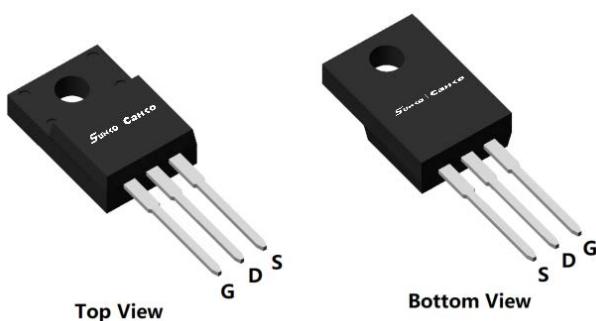
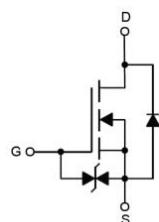


N-Channel Enhancement Mode Field Effect Transistor**ITO-220AB****Product Summary**

- V_{DS} 650V
- I_D 5A
- $R_{DS(ON)}$ (at $V_{GS}=10V$) $<2.8\Omega$
- 100% EAS Tested
- 100% ∇V_{DS} Tested

General Description

- Low Power Loss by High Speed Switching and Low On-Resistance
- Epoxy Meets UL 94 V-0 Flammability Rating
- Halogen Free

Applications

- Power switching application
- Adapter
- PFC Power Supply Stages

■ Absolute Maximum Ratings ($T_A=25^\circ C$ unless otherwise noted)

Parameter	Symbol	Limit	Unit
Drain-source Voltage	V_{DS}	650	V
Gate-source Voltage	V_{GS}	± 30	V
Drain Current	I_D	0.48	A
		0.3	
		5	
		3.1	
Pulsed Drain Current ^A	I_{DM}	10	A
Avalanche energy ^B	EAS	216.6	mJ
Total Power Dissipation ^C	P_D	2	W
		0.8	
		62.5	
		25	
Junction and Storage Temperature Range	T_J, T_{STG}	-55~+150	°C

■ Thermal resistance

Parameter	Symbol	Typ	Max	Units
Thermal Resistance Junction-to-Ambient ^D	$R_{\theta JA}$	50	60	°C/W
Thermal Resistance Junction-to-Case	$R_{\theta JC}$	1.6	2	

■ Ordering Information (Example)

PREFERRED P/N	PACKING CODE	Marking	MINIMUM PACKAGE(pcs)	INNER BOX QUANTITY(pcs)	OUTER CARTON QUANTITY(pcs)	DELIVERY MODE
SCF05N65HX	B1	SCF05N65HX	50	/	5000	Tube

■ Electrical Characteristics ($T_J=25^\circ\text{C}$ unless otherwise noted)

Parameter	Symbol	Conditions	Min	Typ	Max	Units
Static Parameter						
Drain-Source Breakdown Voltage	BV_{DSS}	$V_{\text{GS}}=0\text{V}, I_{\text{D}}=250\mu\text{A}$	650	-	-	V
Zero Gate Voltage Drain Current	I_{DSS}	$V_{\text{DS}}=650\text{V}, V_{\text{GS}}=0\text{V}$	-	-	1	μA
		$V_{\text{DS}}=650\text{V}, V_{\text{GS}}=0\text{V}, T_J=150^\circ\text{C}$	-	-	100	
Gate-Body Leakage Current	I_{GSS}	$V_{\text{GS}}=\pm30\text{V}, V_{\text{DS}}=0\text{V}$	-	-	±100	nA
Gate Threshold Voltage	$V_{\text{GS}(\text{th})}$	$V_{\text{DS}}=V_{\text{GS}}, I_{\text{D}}=250\mu\text{A}$	2.2	3	3.8	V
Static Drain-Source On-Resistance	$R_{\text{DS}(\text{ON})}$	$V_{\text{GS}}=10\text{V}, I_{\text{D}}=5\text{A}$	-	2.1	2.8	Ω
Diode Forward Voltage	V_{SD}	$I_{\text{S}}=5\text{A}, V_{\text{GS}}=0\text{V}$	-	-	1.2	V
Gate resistance	R_{G}	f=1MHz	-	2.6	-	Ω
Maximum Body-Diode Continuous Current	I_{S}		-	-	5	A
Dynamic Parameters						
Input Capacitance	C_{iss}	$V_{\text{DS}}=325\text{V}, V_{\text{GS}}=0\text{V}, f=1\text{MHz}$	-	718	-	pF
Output Capacitance	C_{oss}		-	17	-	
Reverse Transfer Capacitance	C_{rss}		-	2	-	
Switching Parameters						
Total Gate Charge	Q_{g}	$V_{\text{GS}}=10\text{V}, V_{\text{DS}}=325\text{V}, I_{\text{D}}=5\text{A}$	-	15.7	-	nC
Gate-Source Charge	Q_{gs}		-	5.2	-	
Gate-Drain Charge	Q_{gd}		-	1.5	-	
Reverse Recovery Charge	Q_{rr}	$I_{\text{F}}=5\text{A}, \text{di/dt}=100\text{A/us}$	-	2352	-	uC
Reverse Recovery Time	t_{rr}		-	295	-	ns
Turn-on Delay Time	$t_{\text{D(on)}}$	$V_{\text{GS}}=10\text{V}, V_{\text{DD}}=325\text{V}, I_{\text{D}}=5\text{A}$ $R_{\text{GEN}}=3\Omega$	-	21	-	ns
Turn-on Rise Time	t_{r}		-	17	-	
Turn-off Delay Time	$t_{\text{D(off)}}$		-	13	-	
Turn-off fall Time	t_{f}		-	23	-	

A. Repetitive rating; pulse width limited by max. junction temperature.

B. $T_J=25^\circ\text{C}, V_G=10\text{V}, L=30\text{mH}, I_{AS}=3.8\text{A}$.C. P_d is based on max. junction temperature, using junction-case and junction-ambient thermal resistance.D. The value of R_{GJA} is measured with the device mounted on the 40mm*40mm*1.1mm FR-4 PCB board with 1 in² pad of 2oz. Copper, in the still air environment with TA = 25°C. The maximum allowed junction temperature of 150°C. The value in any given application depends on the user's specific board design.

■ Typical Electrical and Thermal Characteristics Diagrams

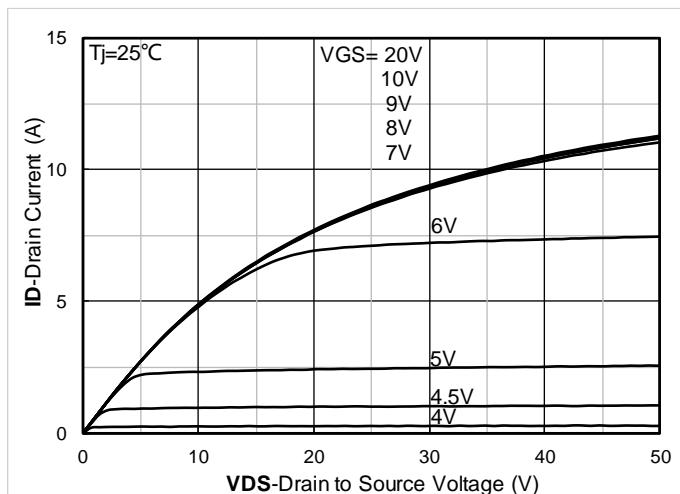


Figure 1. Output Characteristics

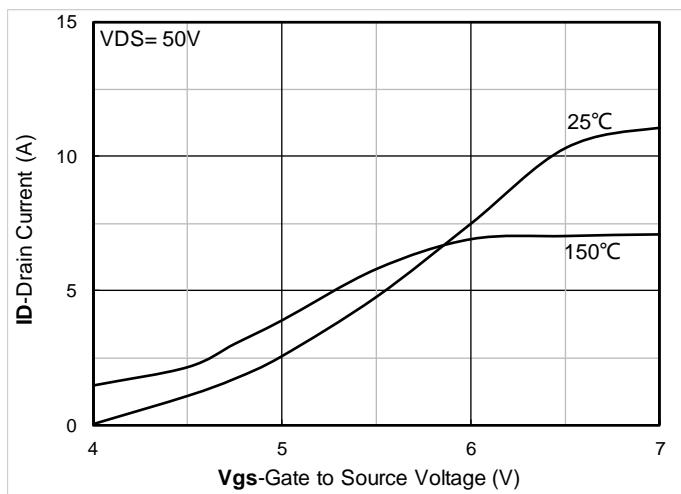


Figure 2. Transfer Characteristics

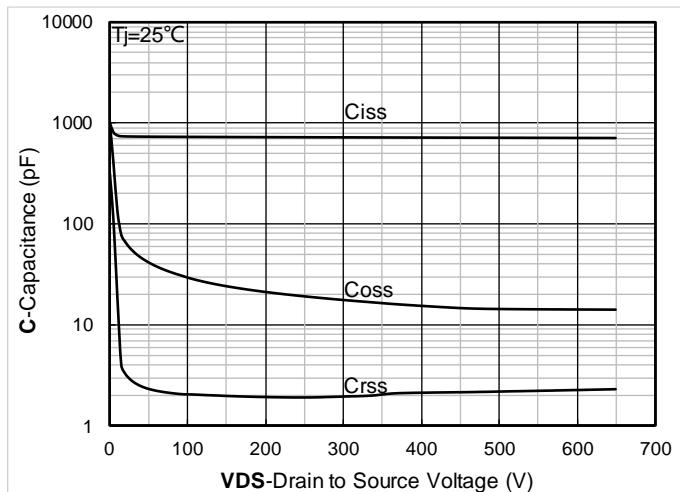


Figure 3. Capacitance Characteristics

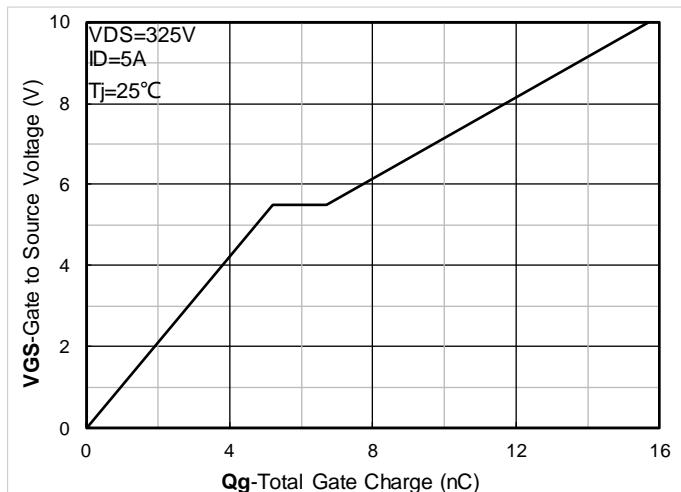


Figure 4. Gate Charge

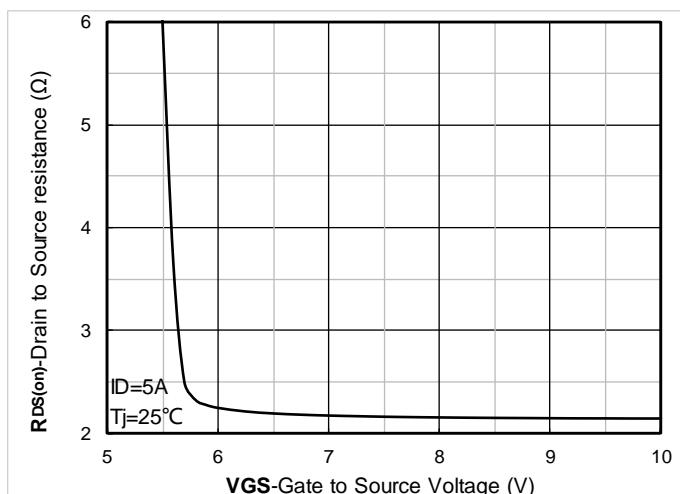


Figure 5. On-Resistance vs Gate to Source Voltage

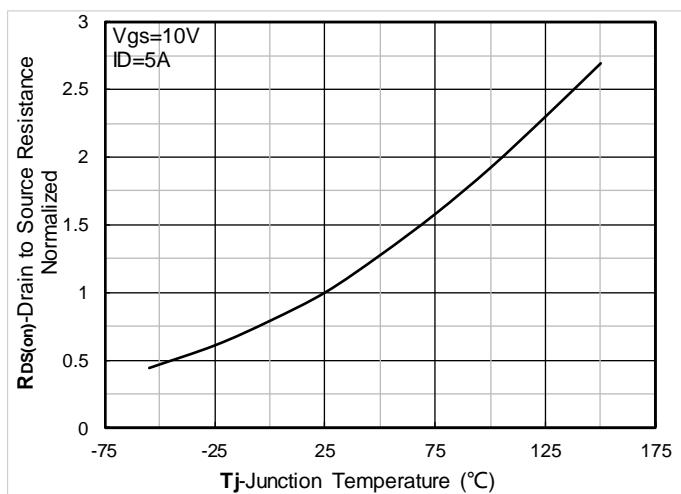


Figure 6. Normalized On-Resistance

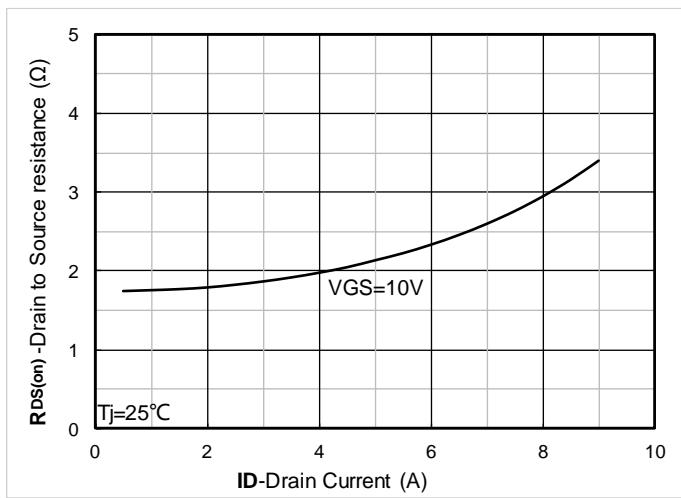


Figure 7. RDS(on) VS Drain Current

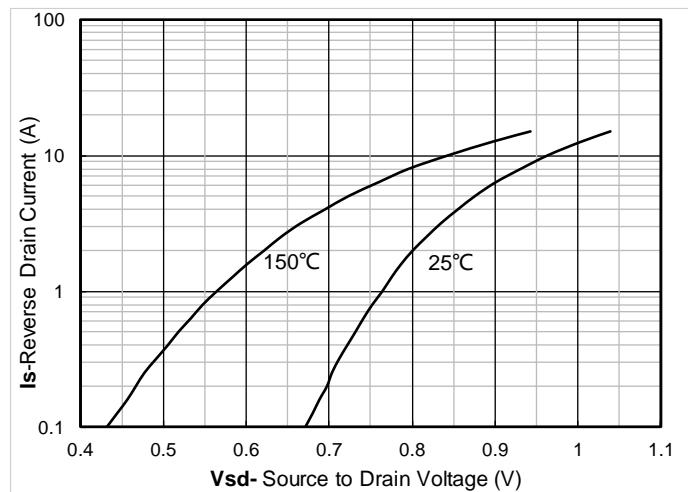


Figure 8. Forward characteristics of reverse diode

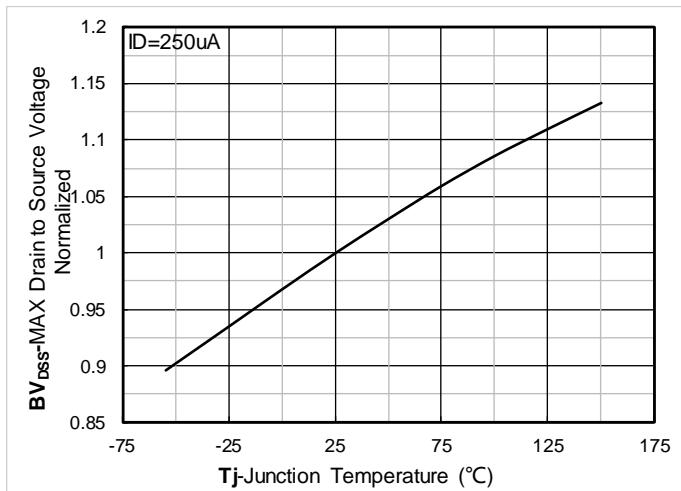


Figure 9. Normalized breakdown voltage

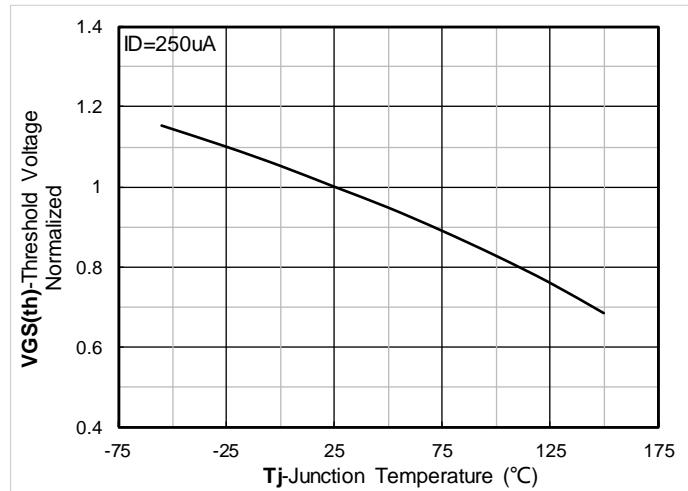


Figure 10. Normalized Threshold voltage

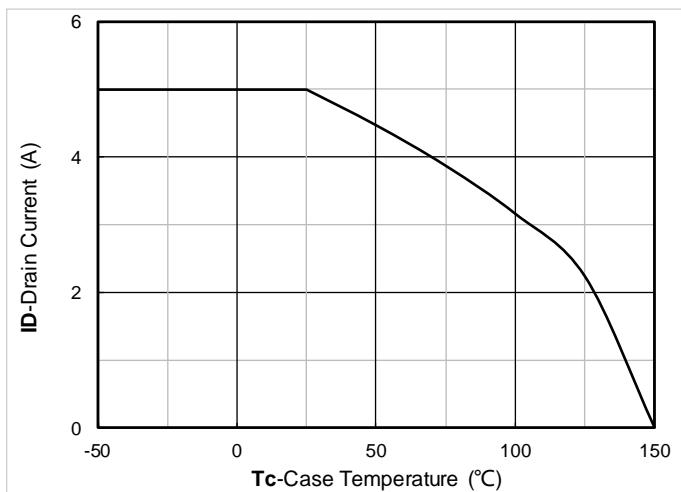


Figure 11. Current dissipation

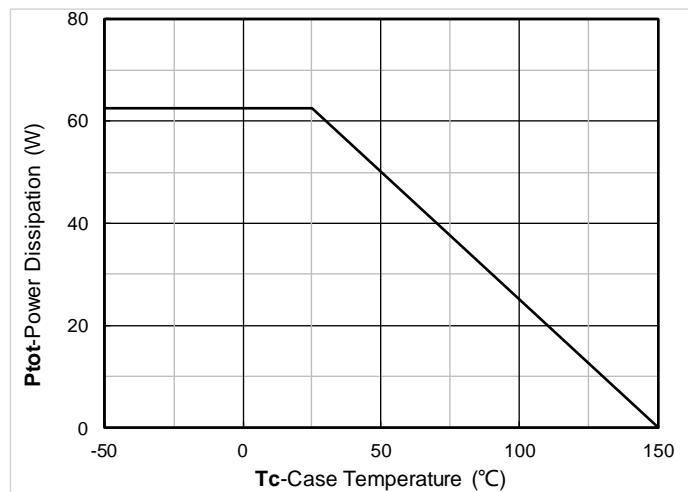


Figure 12. Power dissipation

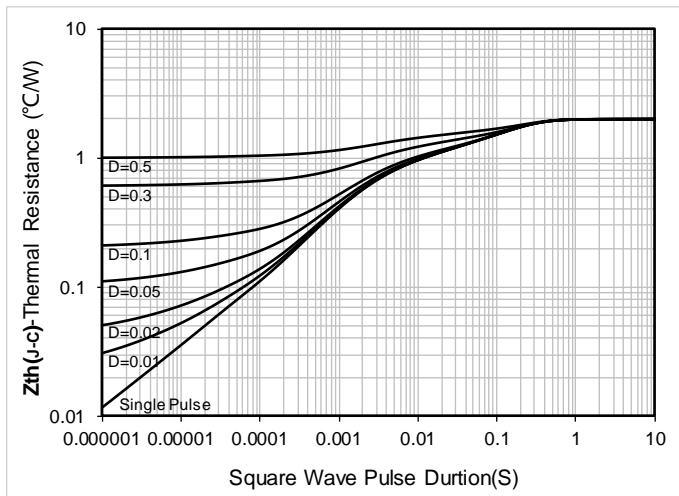


Figure 13. Maximum Transient Thermal Impedance

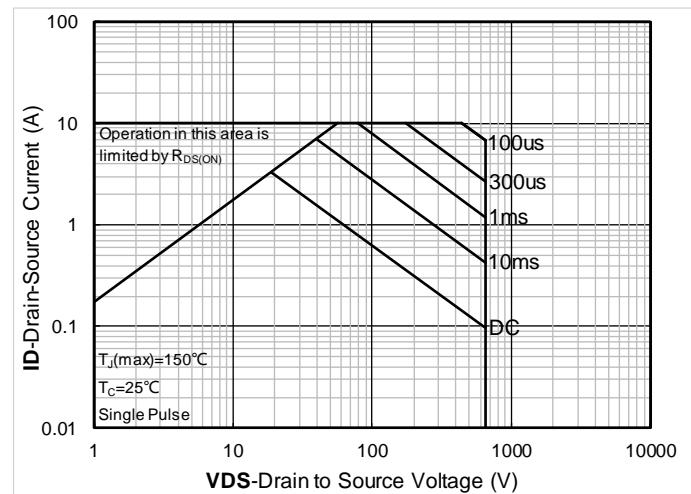


Figure 14. Safe Operation Area

■ Test Circuits & Waveforms

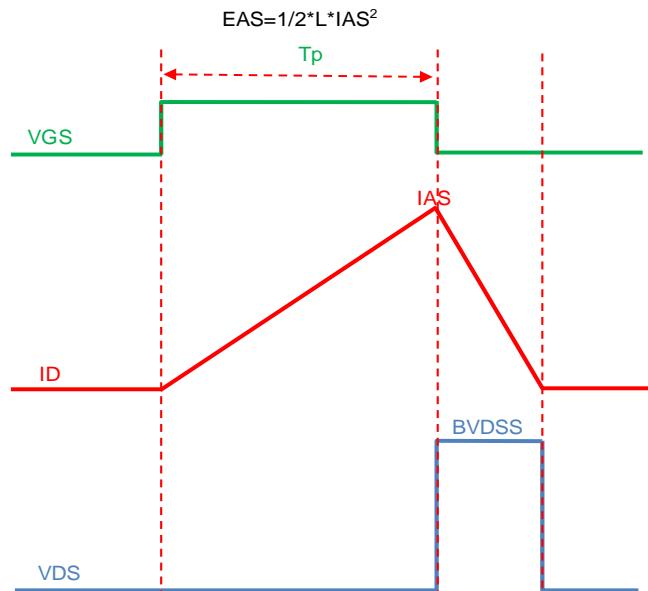
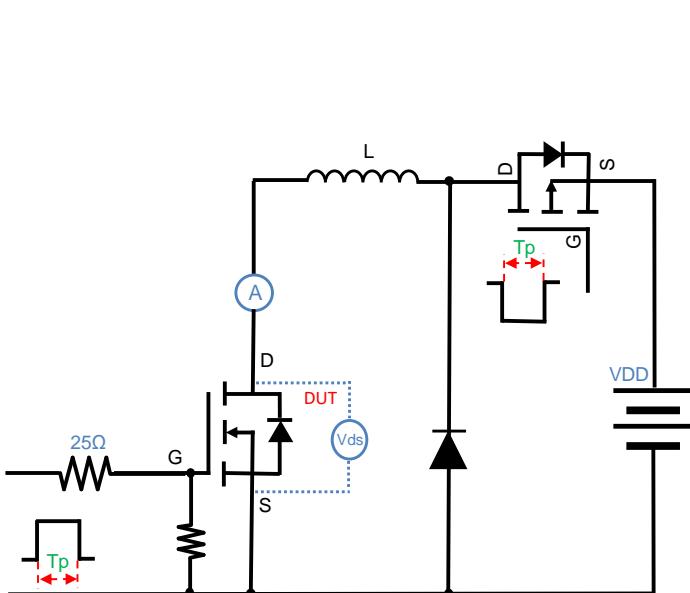


Figure A. Unclamped Inductive Switching (UIS) Test Circuit & Waveform

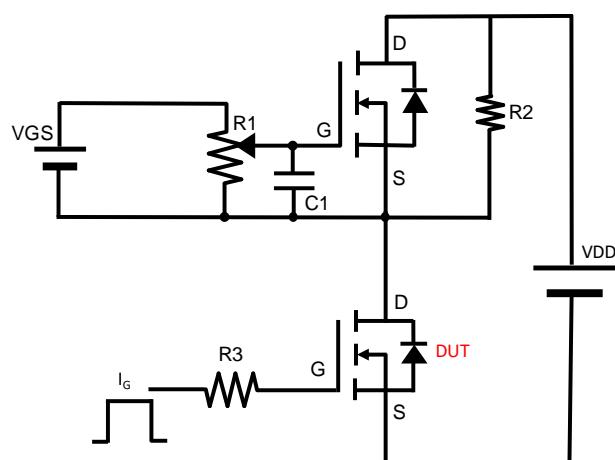


Figure B. Gate Charge Test Circuit & Waveform

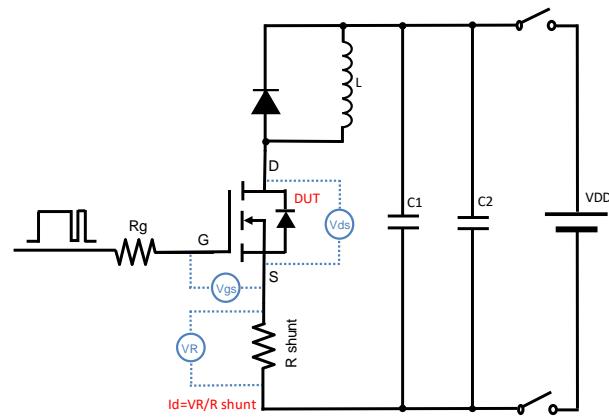


Figure C. Resistive Switching Test Circuit & Waveform

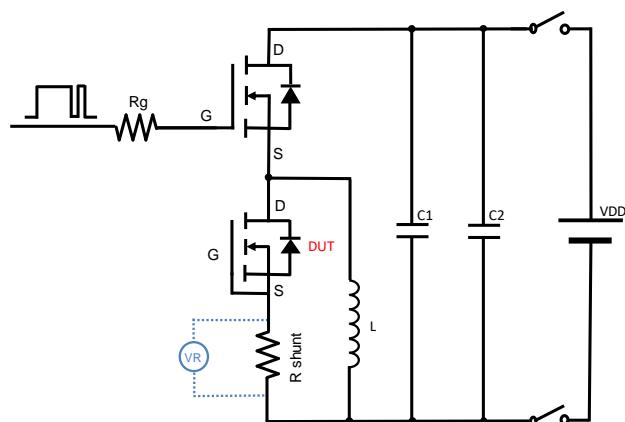
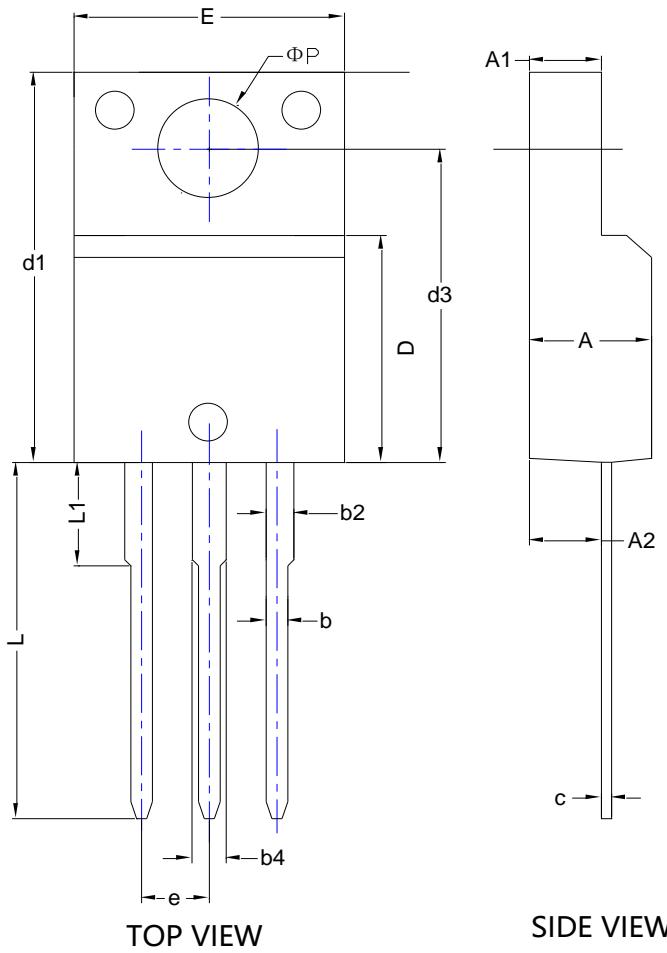


Figure D. Diode Recovery Test Circuit & Waveform

■ ITO-220AB-D Package information



DIMENSIONS				
SYMBOL	INCHES		Millimeter	
	MIN.	MAX.	MIN.	MAX.
A	0.180	0.190	4.57	4.83
A1	0.101	0.111	2.57	2.83
A2	0.099	0.115	2.51	2.93
b	0.024	0.037	0.61	0.94
b2	0.030	0.050	0.76	1.27
b4	0.040	0.060	1.02	1.52
c	0.013	0.025	0.33	0.63
D	0.341	0.386	8.66	9.80
d1	0.622	0.635	15.80	16.13
d3	0.484	0.509	12.30	12.93
E	0.379	0.423	9.63	10.75
e	0.100 BSC.		2.54 BSC.	
L	0.520	0.540	13.20	13.72
L1	0.122	0.145	3.37	3.67
ΦP	0.120	0.136	3.05	3.45

NOTE:

**1.PACKAGE BODY SIZES EXCLUDE MOLD FLASH AND GATE BURRS.
2.TOLERANCE 0.1mm UNLESS OTHERWISE SPECIFIED.**

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